

Tunable Millimeter-Wave Packaged IMPATT Diode Oscillators

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Broadband mechanically tunable V-band (50-75 GHz) and W-band (75-110 GHz) IMPATT oscillators have been developed using packaged silicon p+n junction diodes. A tuning bandwidth of 20% with minimum output of over 50 mW is obtained in V-band and 6% bandwidth with minimum output over 25 mW is obtained in W-band. Higher power but more limited tuning bandwidth results from using other diode structures.

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